TY Semicondutor® TY

2SK1828

SOT-23　　　　Unit: mm

1 GATE
2 SOURCE
3 DRAIN
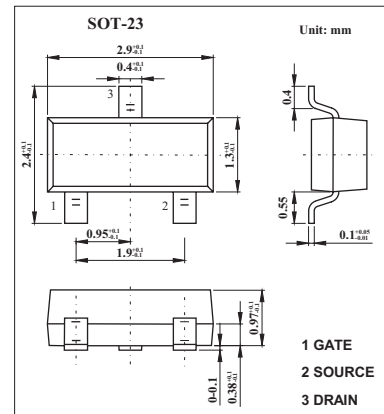
■ Features

● 2.5V Gate Drive

● Low Threshold Voltage :V_{th}=0.5 to 1.5V

● High Speed

■ Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Rating	Unit
Drain to source voltage	V_{DSS}	20	V
Gate to source voltage	V_{GSS}	10	V
Drain current	I_D	50	mA
Power dissipation	P_D	200	m W
Channel temperature	T_{ch}	150	℃
Storage temperature	T_{stg}	-55 to +150	℃

* PW≤ 10ms, duty cycle ≤ 5%

■ Electrical Characteristics Ta = 25℃

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Drain source breakdown voltage	V_{DSS}	I_D=100μA,V_{GS}=0	20			V
Drain cut-off current	I_{DSS}	V_{DS}=20V,V_{GS}=0			1.0	μA
Gate leakage current	I_{GSS}	V_{GS}=10V,V_{DS}=0			1	μA
Forward transfer admittance	$|Y_{fs}|$	V_{DS}=3.0V,I_D=10mA	20			ms
Drain to source on-state resistance	$R_{DS(on)}$	V_{GS}=2.5V,I_D=10mA		25	40	Ω
Input capacitance	C_{iss}	V_{DS}=3.0V,V_{GS}=0,f=1MHZ		5.5		pF
Output capacitance	C_{oss}			1.6		pF
Reverse transfer capacitance	C_{rss}			6.5		pF
Switching time turn on time	ton	I_D=10mA,$V_{GS(on)}$=0 to 2.5V,V_{DD}=3.0V		0.14		μs
Switching time turn off time	toff			0.14		μs

■ Marking

Marking	KI